



Data Sheet

October 1998 File Number 2266.1

11.5A, 400V, 0.400 Ohm, N-Channel Power MOSFET

This is an N-Channel enhancement mode silicon gate power field effect transistor designed for applications such as switching regulators, switching converters, motor drivers, relay drivers, and drivers for high power bipolar switching transistors requiring high speed and low gate drive power. This type can be operated directly from integrated circuits.

Formerly developmental type TA17434.

Ordering Information

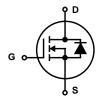
PART NUMBER	PACKAGE	BRAND
BUZ351	TO-218AC	BUZ351

NOTE: When ordering, use the entire part number.

Features

- 11.5A, 400V
- r_{DS(ON)} = 0.400Ω
- SOA is Power Dissipation Limited
- Nanosecond Switching Speeds
- Linear Transfer Characteristics
- High Input Impedance
- Majority Carrier Device
- Related Literature
 - TB334 "Guidelines for Soldering Surface Mount Components to PC Boards"

Symbol



Packaging

JEDEC TO-218AC

